

**Список основных публикаций официального оппонента  
Карасёва Платона Александровича в рецензируемых научных изданиях  
по теме диссертации за последние 5 лет**

1. A.I. Titov, **P.A. Karaseov**, K.V. Karabeshkin, A.I. Struchkov, “The formation of radiation damage in GaN during successive bombardment by light ions of various energies”, *Vacuum* 173, 109149 (2020).
2. A.I. Titov, K.V. Karabeshkin, **P.A. Karaseov**, A.I. Struchkov, “Do Chemical Effects Affect the Accumulation of Structural Damage during the Implantation of Fluorine Ions into GaN?”, *Semiconductors* 53, 1415–1418 (2019).
3. A.I. Titov, **P.A. Karaseov**, K.V. Karabeshkin, G.M. Ermolaeva, V.B. Shilov, “Effect of monatomic and molecular ion irradiation on time resolved photoluminescence decay in GaN”, *Nucl. Instrum. Meth. Phys. Res. B* 458, 164–168 (2019).
4. V.V. Kozlovski, A.E. Vasil’ev, **P.A. Karaseov**, A.A. Lebedev, “Formation of Radiation Defects by Proton Braking in Lightly Doped n- and p-SiC Layers” *Semiconductors* 52, 310–315 (2018).
5. **P.A. Karaseov**, K.V. Karabeshkin, A.I. Titov, M.W. Ullah, A. Kuronen, F. Djurabekova, K. Nordlund, G.M. Ermolaeva, V.B. Shilov, “Single and molecular ion irradiation-induced effects in GaN: experiment and cumulative MD simulations”, *Journal of Physics D: Applied Physics* 50 (50), 505110 (2017).
6. V.P. Popov, M.A. Ilnitskii, G.P. Pokhil, A.I. Titov, **P.A. Karaseov**, K.V. Karabeshkin, Yu.N. Pal’yanov, S. Rubanov, “Ranges of 10–350keV H and H<sub>2</sub> ions in (111) diamond”, *Nucl. Instrum. Meth. Phys. Res. B* 406, 634-637 (2017).